eagleyard

Revision 0.70

SINGLE FREQUENCY LASER DIODES Distributed Bragg Reflector Laser with integrated Amplifier



Product	Application
1064 nm DBR Laser	Raman Spectroscopy
with monolithically integrated Tapered Amplifier (TA)	Metrology
hermetic 14 Pin Butterfly Housing (RoHS compliant)	Nd:YAG Replacement
including Thermoelectric Cooler and Thermistor	EDFA Pumping

Absolute Maximum Ratings

General Product Information

Parameter	Symbol	Unit	min	typ	max
Storage Temperature	Ts	°C	-40		85
Operational Temperature at Case	T _C	°C	-20		75
Operational Temperature at Laser Chip	T _{LD}	°C	10		50
Forward Current DBR	I _{DBR}	mA			500
Forward Current TA	I _{TA}	А			7.5
Reverse Voltage DBR	V _{R DBR}	V			2
Reverse Voltage TA	V _{R TA}	V			2
Output Power	P _{opt}	W			2.5
TEC Current	I _{TEC}	А			2.5
TEC Voltage	V _{TEC}	V			5.0
-					

Recommended Operational Conditions

Parameter	Symbol	Unit	min	typ	max
Operational Temperature at Case	T _C	°C	0		50
Operational Temperature at Laser Chip	T _{LD}	°C	15	25	35
Forward Current DBR	I _{DBR}	mA			450
Forward Current TA	I _{TA}	А			7.0
Output Power	P _{opt}	W			2.0

Characteristics

Parameter	Symbol	Unit	min	typ	max
Center Wavelength	λ_{C}	nm	1063	1064	1065
Spectral Width (FWHM)	Δλ	pm		3	
Sidemode Supression Ratio	SMSR	dB	30		



μΜΟΡΑ

Measurement Conditions / Comments

Stress in excess of one of the Absolute Maximum Ratings may damage the laser. Please note that a damaging optical power level may occur although the maximum current is not reached. These are stress ratings only, and functional operation at these or any other conditions beyond those indicated under Recommended Operational Conditions is not implied.

Measurement Conditions / Comments

Measurement Conditions / Comments

see images on page 4

apart from mode-hops (see Spectral Map on page 4) $P_{opt}=\,2$ W







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Characteristics					cont'd
Parameter	Symbol	Unit	min	typ	max
Temperature Coefficient of Wavelength	dλ / dT	nm / K		0.08	
Current Coefficient of Wavelength	d λ / dI _{DBR}	nm / mA		0.001	
Current Coefficient of Wavelength	d λ / dI _{TA}	nm / A		0.035	
Laser Current @ $P_{opt} = 2.0 \text{ W}$	I _{TA}	А			7.0
Slope Efficiency	η	W/A		0.8	
Threshold Current	I _{th TA}	А		3	
Divergence parallel (FWHM)	$\Theta_{ }$	mrad		2	
Divergence perpendicular (FWHM)	Θ_{\perp}	mrad		2	
Beam Diameter horizontal (1/e ²)	d	mm		1	
Beam Diameter vertical (1/e ²)	d_\perp	mm		1	
Degree of Polarization	DOP	%		90	

Measurement Conditions / Comments Laser Forward Current DBR Laser Forward Current TA Amplifier parallel to the base plate of the housing (see p. 3) perpendicular to base plate of the housing (see p. 3) parallel to the base plate of the housing (see p. 3) perpendicular to base plate of the housing (see p. 3) $P_{opt} = 2$ W; E field parallel to the base plate

Thermoelectric Cooler

Parameter	Symbol	Unit	min	typ	max
Current	I _{TEC}	А			2.5
Voltage	U_{TEC}	V			5.0
Power Dissipation (total loss at case)	Ploss	W		10	
Temperature Difference	ΔT	К			25

Thermistor (Standard NTC Type)

	Unit	min	typ	max
R	kΩ		10	
β			3892	
А			1.1293 x 10	-3
В			2.3410 x 10	-4
С			8.7755 x 10	-8
	β A	β A	β A B	β 3892 A 1.1293 x 10

Measurement Conditions / Comments				
$P_{opt} = 2 \text{ W}, \Delta T = 20 \text{ K}$				
$P_{opt} = 2 \text{ W}, \Delta T = 20 \text{ K}$				
$P_{opt} = 2 \text{ W}, \Delta T = 20 \text{ K}$				
$P_{opt} = 2 \text{ W}, \Delta T = \text{Tcase} - \text{TLD} $				

Measurement Conditions / Cor	ninents
$\Gamma_{LD} = 25^{\circ} C$	
$R_1 / R_2 = e^{\beta (1/T_1 - 1/T_2)}$ at $T_{LD} =$	0° 50° C
$/T = A + B(\ln R) + C(\ln R)^3$	
: temperature in Kelvin	
R: resistance at T in Ohm	





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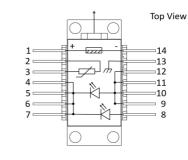
2/4

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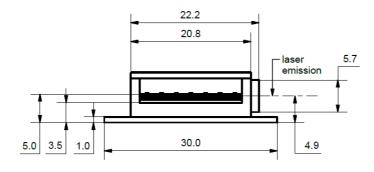
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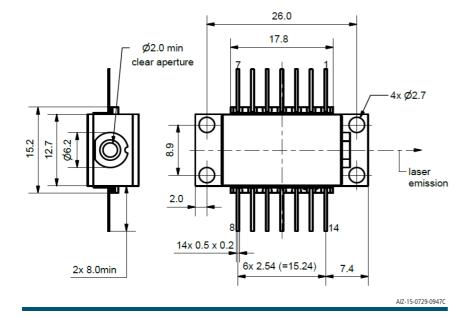
Pin Assignment

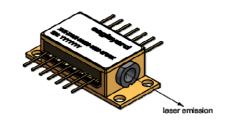
1	Thermoelectric Cooler (+)	14	Thermoelectric Cooler (-)
2	Thermistor	13	Case
3	Thermistor	12	Amplifier (Anode)
4	Laser and Amplifier (Cathode)	11	Amplifier (Anode)
5	Laser and Amplifier (Cathode)	10	Amplifier (Anode)
6	Laser and Amplifier (Cathode)	9	Amplifier (Anode)
7	Laser and Amplifier (Cathode)	8	Laser (Anode)



Package Drawings







Caution. Excessive mechanical stress on the package can lead to a damage of the laser.

See <u>instruction manual</u> on www.eagleyard.com

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Spectral Map

Wavelength [nm]

Typical Measurement Results

1065.0

1064.8

1064.6

1064.4

1064.2

1064.0

100

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24.45 -31.45 -38.45 -45.45 notice. 52.45 æ -66.45 -73.45 -80.45

400

-87.45

Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without

Unpacking, Installation and Laser Safety

150

200

250

Forward Current DBR [mA]

300

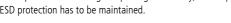
350

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.

The TBR laser is sensitive against optical feedback, so an optical isolator may be required in order to avoid any disturbance of the emission spectrum. Operating at moderate temperatures on proper heat sinks will contribute to a long lifetime of the diode.

Avoid direct and/or indirect exposure to the free running beam. Collimating and focussing the free running beam with optics as common in optical instruments will increase threat to the human eye.

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